

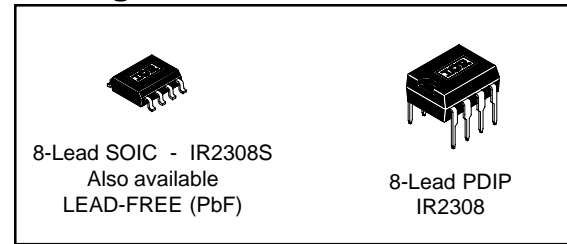
IR2308(S) & (PbF)

HALF-BRIDGE DRIVER

Features

- Floating channel designed for bootstrap operation
 Fully operational to +600V
 Tolerant to negative transient voltage
 dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for both channels
- 3.3V, 5V and 15V input logic compatible
- Cross-conduction prevention logic
- Matched propagation delay for both channels
- Outputs in phase with inputs
- Logic and power ground +/- 5V offset.
- Internal 540ns dead-time
- Lower di/dt gate driver for better noise immunity
- Also available LEAD_FREE

Packages



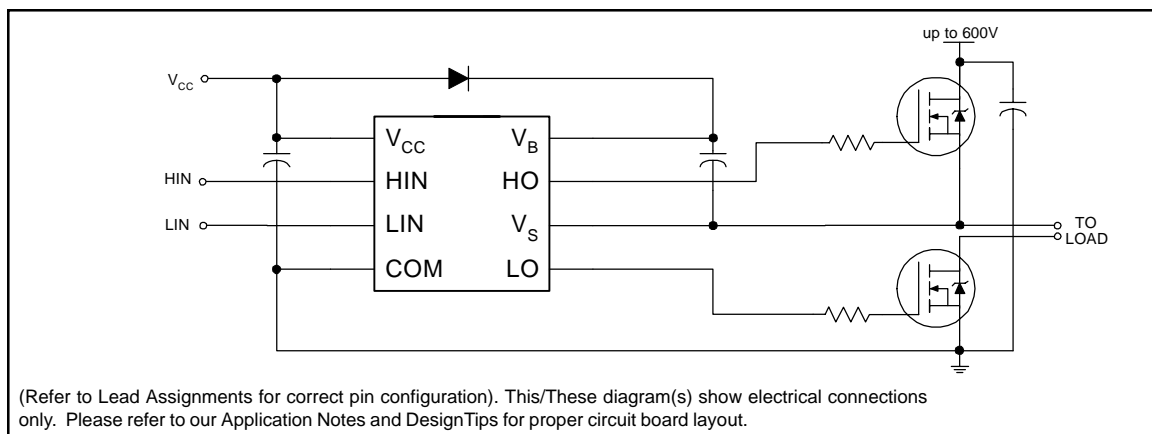
2106//2108//2109/2304/2308 Feature Comparison

| Part | Input logic | Cross-conduction prevention logic | Dead-Time | Ground Pins |
|-------|-------------|-----------------------------------|--|-------------|
| 2106 | HIN/LIN | no | none | COM |
| 21064 | | | | VSS/COM |
| 2108 | HIN/LIN | yes | Internal 540ns Programmable 0.54-5 μs | COM |
| 21084 | | | | VSS/COM |
| 2109 | IN/SD | yes | Internal 540ns Programmable 0.54-5 μs | COM |
| 21094 | | | | VSS/COM |
| 2304 | HIN/LIN | yes | Internal 100ns | COM |
| 2308 | HIN/LIN | yes | Internal 540ns | COM |

Description

The IR2308(S) are high voltage, high speed power MOSFET and IGBT drivers with dependent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.

Typical Connection



IR2308(S) & (PbF)

Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

| Symbol | Definition | Min. | Max. | Units | |
|---------------------|--|-----------------------|-----------------------|-------|------|
| V _B | High side floating absolute voltage | -0.3 | 625 | V | |
| V _S | High side floating supply offset voltage | V _B - 25 | V _B + 0.3 | | |
| V _{HO} | High side floating output voltage | V _S - 0.3 | V _B + 0.3 | | |
| V _{CC} | Low side and logic fixed supply voltage | -0.3 | 25 | | |
| V _{LO} | Low side output voltage | -0.3 | V _{CC} + 0.3 | | |
| V _{IN} | Logic input voltage (HIN & LIN) | V _{SS} - 0.3 | V _{CC} + 0.3 | | |
| dV _S /dt | Allowable offset supply voltage transient | — | 50 | V/ns | |
| P _D | Package power dissipation @ T _A ≤ +25°C | (8 lead PDIP) | — | 1.0 | W |
| | | (8 lead SOIC) | — | 0.625 | |
| R _{thJA} | Thermal resistance, junction to ambient | (8 lead PDIP) | — | 125 | °C/W |
| | | (8 lead SOIC) | — | 200 | |
| T _J | Junction temperature | — | 150 | °C | |
| T _S | Storage temperature | -50 | 150 | | |
| T _L | Lead temperature (soldering, 10 seconds) | — | 300 | | |

Recommended Operating Conditions

The Input/Output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The V_S and V_{SS} offset rating are tested with all supplies biased at 15V differential.

| Symbol | Definition | Min. | Max. | Units |
|-----------------|--|---------------------|---------------------|-------|
| V _B | High side floating supply absolute voltage | V _S + 10 | V _S + 20 | V |
| V _S | High side floating supply offset voltage | Note 1 | 600 | |
| V _{HO} | High side floating output voltage | V _S | V _B | |
| V _{CC} | Low side and logic fixed supply voltage | 10 | 20 | |
| V _{LO} | Low side output voltage | 0 | V _{CC} | |
| V _{IN} | Logic input voltage | COM | V _{CC} | |
| T _A | Ambient temperature | -40 | 125 | °C |

Note 1: Logic operational for V_S of -5 to +600V. Logic state held for V_S of -5V to -V_{BS}. (Please refer to the Design Tin DT97-3 for more details).

Dynamic Electrical Characteristics

V_{BIAS} (V_{CC} , V_{BS}) = 15V, V_{SS} = COM, C_L = 1000 pF, T_A = 25°C, DT = V_{SS} unless otherwise specified.

| Symbol | Definition | Min. | Typ. | Max. | Units | Test Conditions |
|-----------|--|------|------|------|-------|----------------------|
| t_{on} | Turn-on propagation delay | — | 220 | 300 | nsec | $V_S = 0V$ |
| t_{off} | Turn-off propagation delay | — | 200 | 280 | | $V_S = 0V$ or $600V$ |
| MT | Delay matching $t_{on} - t_{off}$ | — | 0 | 46 | | |
| t_r | Turn-on rise time | — | 150 | 220 | | $V_S = 0V$ |
| t_f | Turn-off fall time | — | 50 | 80 | | $V_S = 0V$ |
| DT | Deadtime: LO turn-off to HO turn-on(DT _{LO-HO}) & HO turn-off to LO turn-on (DT _{HO-LO}) | 400 | 540 | 680 | | |
| MDT | Deadtime matching = DT _{LO-HO} - DT _{HO-LO} | — | 0 | 60 | | |

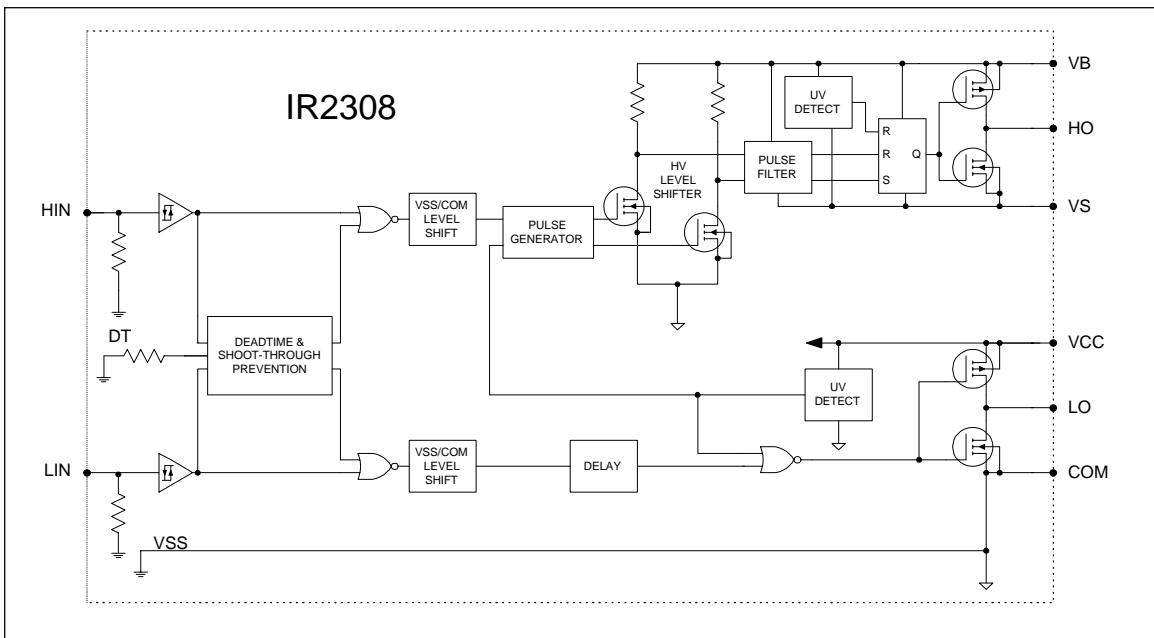
Static Electrical Characteristics

V_{BIAS} (V_{CC} , V_{BS}) = 15V, V_{SS} = COM, DT = V_{SS} and T_A = 25°C unless otherwise specified. The V_{IL} , V_{IH} and I_{IN} parameters are referenced to V_{SS}/COM and are applicable to the respective input leads: HIN and LIN. The V_O , I_O and R_{on} parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

| Symbol | Definition | Min. | Typ. | Max. | Units | Test Conditions |
|----------------------------|--|------|------|------|---------|---------------------------------------|
| V_{IH} | Logic "1" input voltage for HIN & LIN | 2.9 | — | — | V | $V_{CC} = 10V$ to $20V$ |
| V_{IL} | Logic "0" input voltage for HIN & LIN | — | — | 0.8 | | $V_{CC} = 10V$ to $20V$ |
| V_{OH} | High level output voltage, $V_{BIAS} - V_O$ | — | 0.8 | 1.4 | | $I_O = 20$ mA |
| V_{OL} | Low level output voltage, V_O | — | 0.3 | 0.6 | | $I_O = 20$ mA |
| I_{LK} | Offset supply leakage current | — | — | 50 | μA | $V_B = V_S = 600V$ |
| I_{QBS} | Quiescent V_{BS} supply current | 20 | 60 | 150 | μA | $V_{IN} = 0V$ or $5V$ |
| I_{QCC} | Quiescent V_{CC} supply current | 0.4 | 1.0 | 1.6 | mA | $V_{IN} = 0V$ or $5V$ |
| I_{IN+} | Logic "1" input bias current | — | 5 | 20 | μA | HIN = 5V, LIN = 5V |
| I_{IN-} | Logic "0" input bias current | — | 1 | 2 | | HIN = 0V, LIN = 0V |
| V_{CCUV+} V_{BSUV+} | V_{CC} and V_{BS} supply undervoltage positive going threshold | 8.0 | 8.9 | 10 | V | |
| V_{CCUV-} V_{BSUV-} | V_{CC} and V_{BS} supply undervoltage negative going threshold | 7.4 | 8.2 | 9.0 | | |
| V_{CCUVH} V_{BSUVH} | Hysteresis | 0.3 | 0.7 | — | | |
| I_{O+} | Output high short circuit pulsed current | 97 | 200 | — | mA | $V_O = 0V$, PW ≤ 10 μs |
| I_{O-} | Output low short circuit pulsed current | 250 | 350 | — | | $V_O = 15V$, PW ≤ 10 μs |

IR2308(S) & (PbF)

Functional Block Diagram



Lead Definitions

| Symbol | Description |
|-----------------|---|
| HIN | Logic input for high side gate driver output (HO), in phase |
| LIN | Logic input for low side gate driver output (LO), in phase |
| V _B | High side floating supply |
| HO | High side gate driver output |
| V _S | High side floating supply return |
| V _{CC} | Low side and logic fixed supply |
| LO | Low side gate driver output |
| COM | Low side return |

Lead Assignments

| | |
|--------------------|---|
| <p>8 Lead PDIP</p> | <p>8 Lead SOIC Also available LEAD-FREE(PbF)</p> |
| IR2308 | IR2308S |

IR2308(S) & (PbF)

International
IR Rectifier

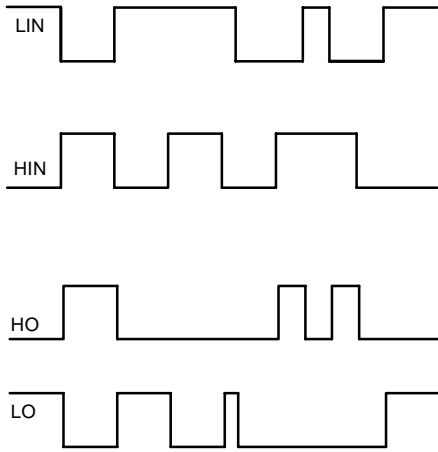


Figure 1. Input/Output Timing Diagram

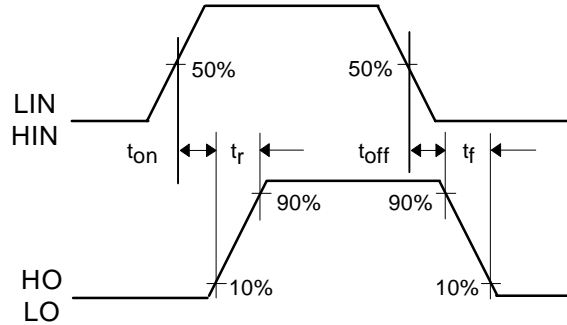


Figure 2. Switching Time Waveform Definitions

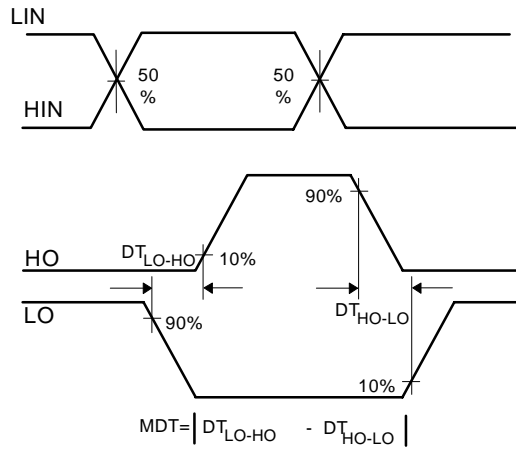
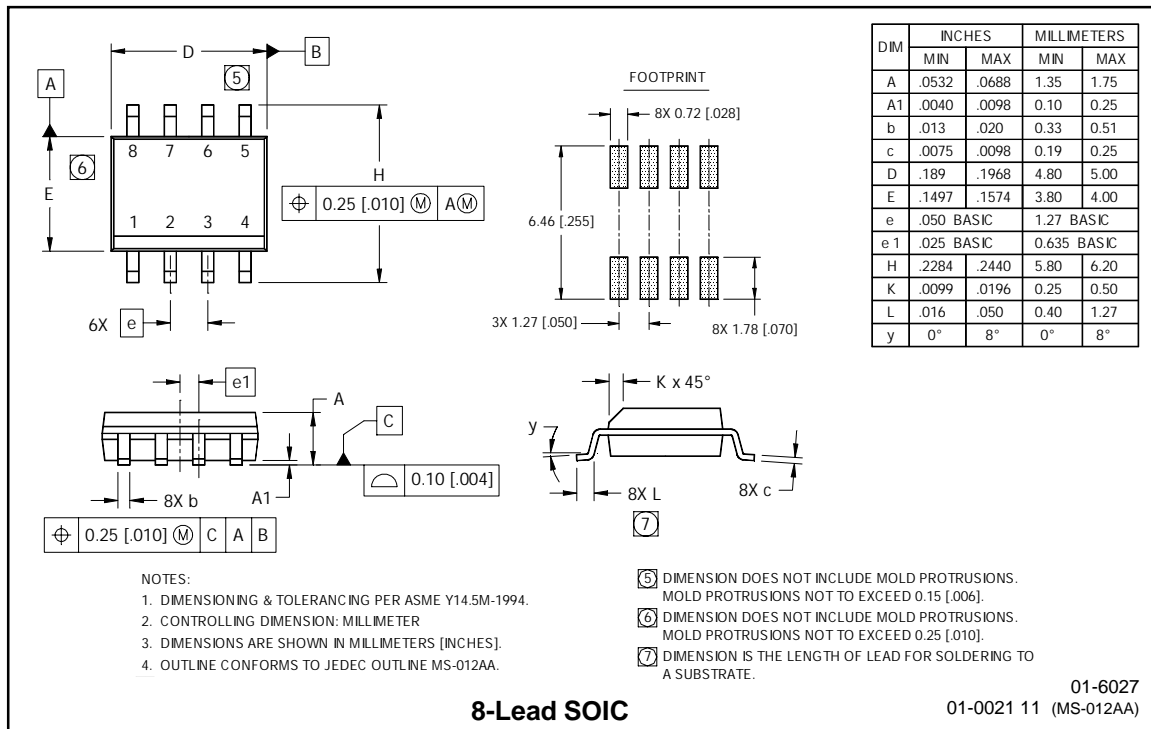
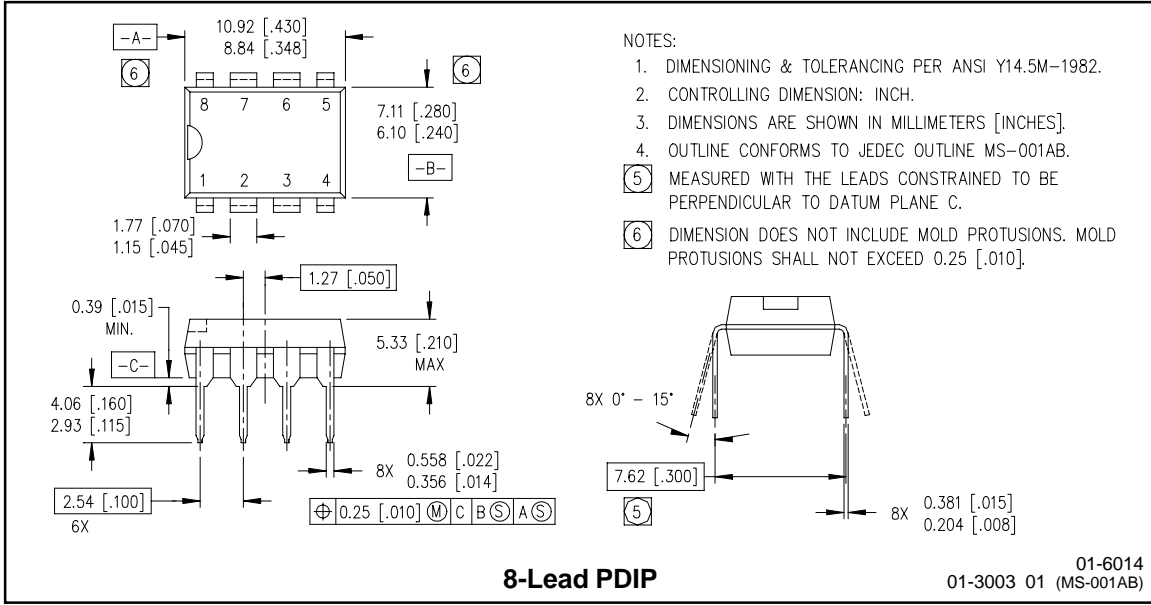


Figure 3. Deadtime Waveform Definitions

International
IR Rectifier

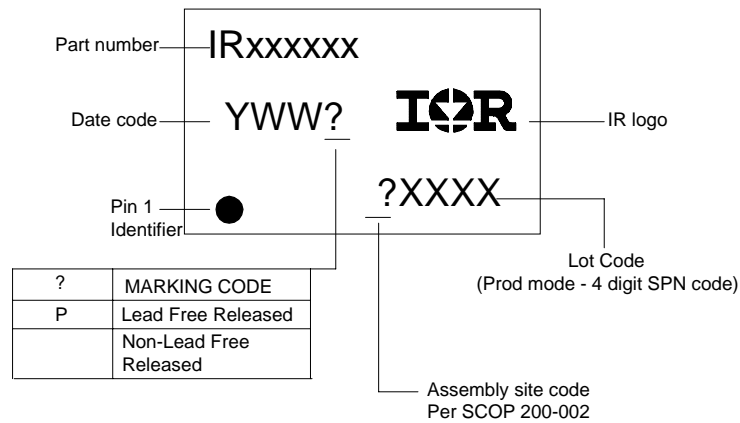
IR WORLD HEADQUARTERS: 233 Kansas Street, El Segundo, California 90245 Tel: (310) 252-7105
Data and specifications subject to change without notice. 3/19/2003

Case outlines



IR2308(S) & (PbF)

LEADFREE PART MARKING INFORMATION



ORDER INFORMATION

Basic Part (Non-Lead Free)

8-Lead PDIP IR2308 order IR2308
8-Lead SOIC IR2308S order IR2308S

Leadfree Part

8-Lead PDIP R2308 not available
8-Lead SOIC IR2308S order IR2308SPbF